

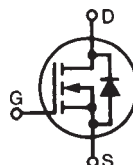
Standard Power MOSFET

IXTH 41N25

$$\begin{aligned} V_{DSS} &= 250 \text{ V} \\ I_{D(\text{cont})} &= 41 \text{ A} \\ R_{DS(\text{on})} &= 72 \text{ m}\Omega \end{aligned}$$

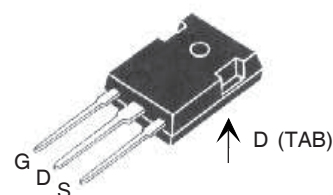
N-Channel Enhancement Mode

Preliminary Data Sheet



Symbol	Test conditions	Maximum ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	250	V
V_{DGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GS} = 1.0 \text{ M}\Omega$	250	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$ MOSFET chip capability	41	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	164	A
I_{AR}		41	A
E_{AR}	$T_C = 25^\circ\text{C}$	30	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	1.0	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$, $R_G = 2 \Omega$	5	V/ns
P_D	$T_C = 25^\circ\text{C}$	300	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight	TO-264	6	g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

TO-247 AD



G = Gate D = Drain
S = Source Tab = Drain

Features

- Low $R_{DS(\text{on})}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- International standard package JEDEC TO-247 AD
- Fast switching times
- High commutating dv/dt rating

Applications

- Motor controls
- DC choppers
- Switched-mode and resonant-mode power supplies
- Uninterruptible Power Supplies (UPS)

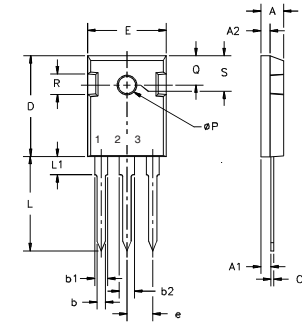
Advantages

- Easy to mount with one screw (isolated mounting screw hole)
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	250		V
$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	2.0		4.0 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V DC}$, $V_{DS} = 0$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			25 μA 250 μA
$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$, $I_D = 15 \text{ A}$ Pulse test, $t \leq 300 \text{ ms}$, duty cycle $d \leq 2\%$	60		72 m Ω

Symbol	Test Conditions	Characteristic values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10 \text{ V}; I_D = 0.5 I_{D25}$, pulse test	20	28	S
C_{iss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		3200	pF
C_{oss}			510	pF
C_{rss}			180	pF
$t_{d(on)}$	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 3.6 \Omega$ (External)		19	ns
t_r			19	ns
$t_{d(off)}$			79	ns
t_f			17	ns
$Q_{g(on)}$	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$		110	nC
Q_{gs}			18	nC
Q_{gd}			48	nC
R_{thJC}		0.25		0.42 K/W
R_{thCK}				K/W

TO-247 AD Outline



Terminals: 1 - Gate
2 - Drain
3 - Source
Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

Source-Drain Diode

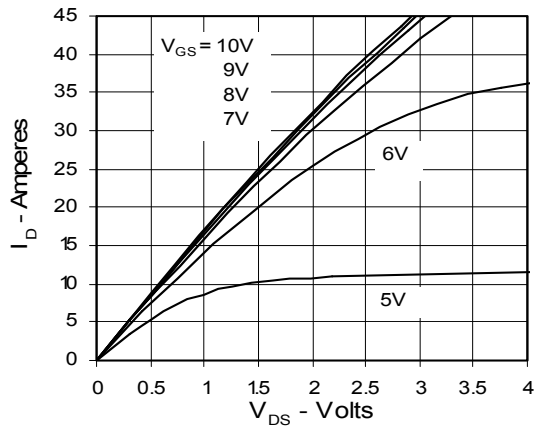
Ratings and Characteristics

($T_J = 25^\circ\text{C}$ unless otherwise specified)

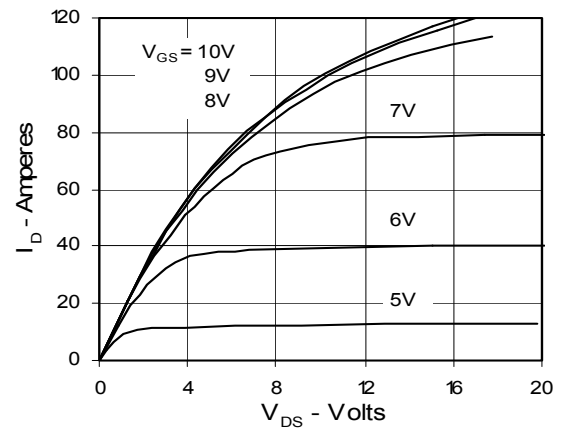
Symbol	Test Conditions	Min.	Typ.	Max.
I_S	$V_{GS} = 0 \text{ V}$			41 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			164 A
V_{SD}	$I_F = I_S, V_{GS} = 0 \text{ V}$, Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$			1.5 V
t_{rr}	$I_F = 0.5 I_S, -di/dt = 100 \text{ A}/\mu\text{s}, V_R = 100 \text{ V}$		300	ns
Q_{rr}			3.0	μC

IXYS reserves the right to change limits, test conditions, and dimensions.

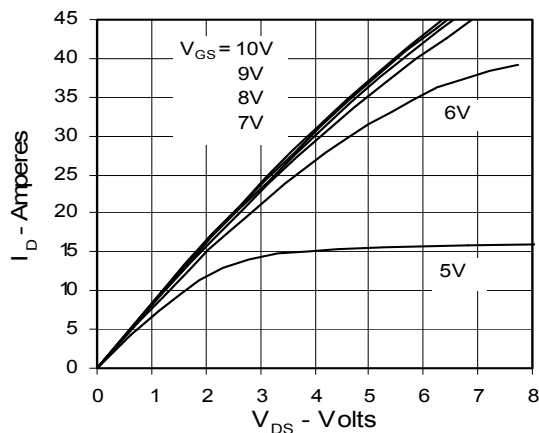
**Fig. 1. Output Characteristics
@ 25 Deg. C**



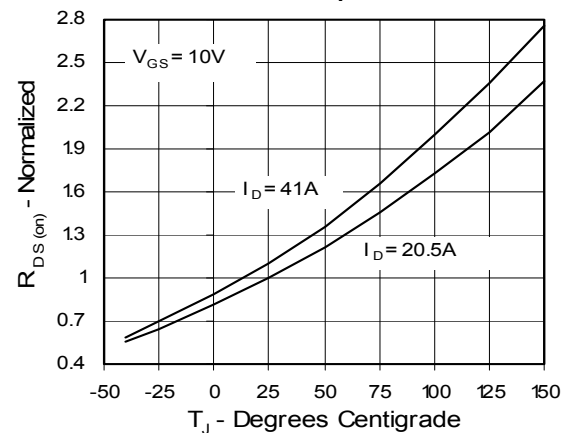
**Fig. 2. Extended Output Characteristics
@ 25 deg. C**



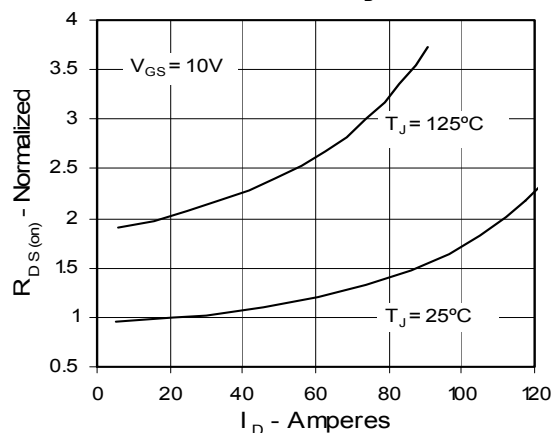
**Fig. 3. Output Characteristics
@ 125 Deg. C**



**Fig. 4. $R_{DS(on)}$ Normalized to I_{D25} Value vs.
Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to I_{D25}
Value vs. I_D**



**Fig. 6. Drain Current vs. Case
Temperature**

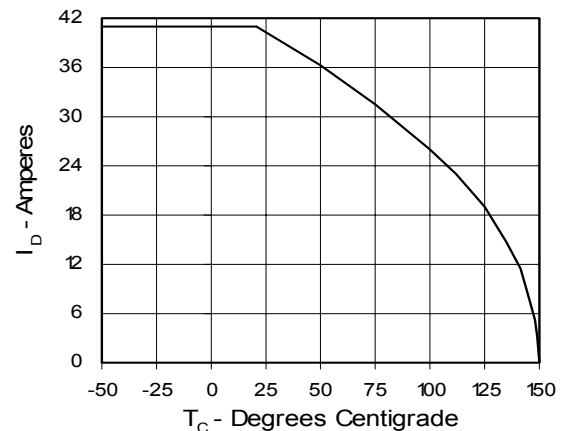


Fig. 7. Input Admittance

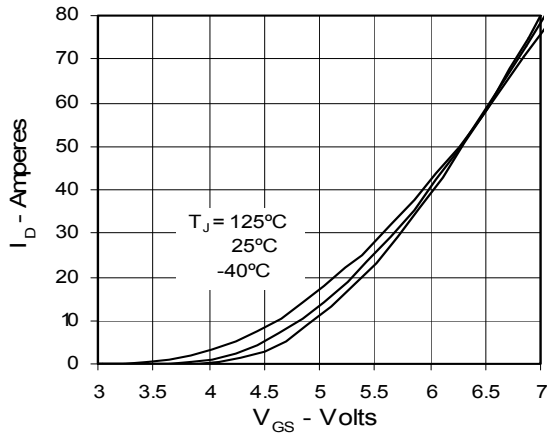


Fig. 8. Transconductance

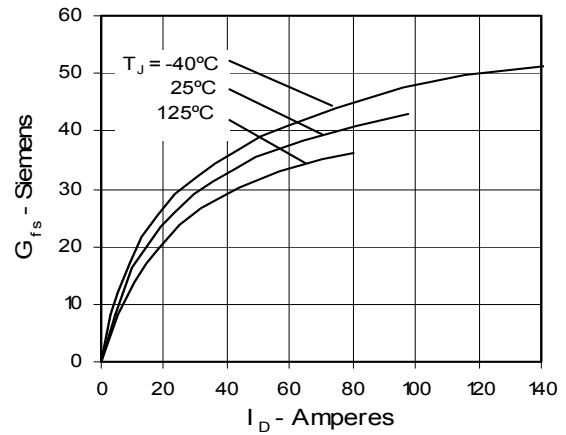


Fig. 9. Source Current vs. Source-To-Drain Voltage

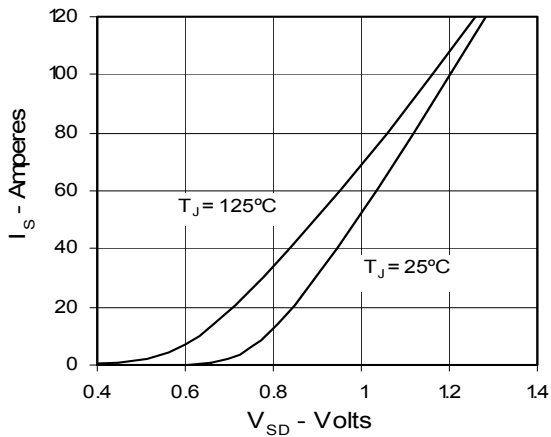


Fig. 10. Gate Charge

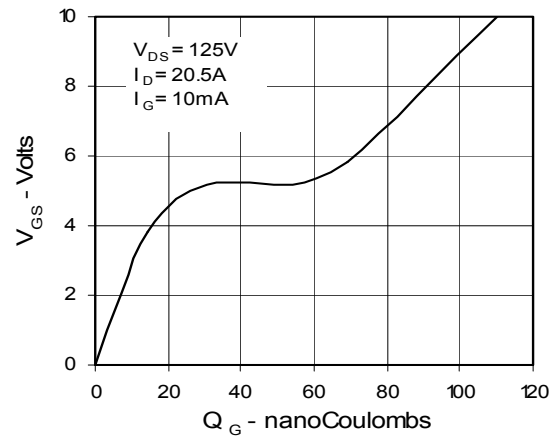


Fig. 11. Capacitance

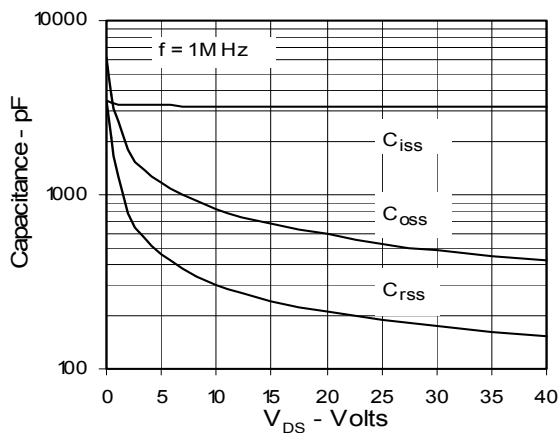
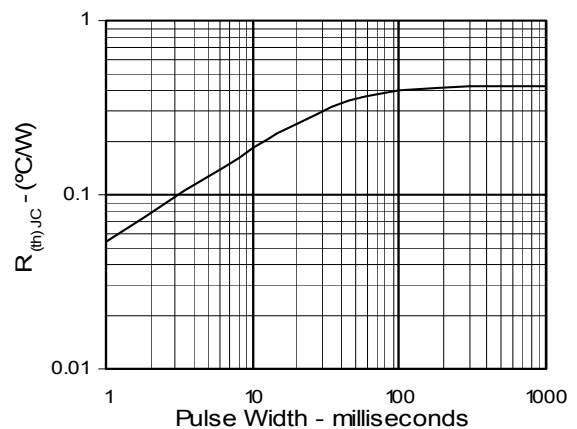


Fig. 12. Maximum Transient Thermal Resistance



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IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1	6,259,123B1	6,306,728B1
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	6,404,065B1	6,162,665	6,534,343